

1N4148WT

Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- Ultra-small surface mount package
- For general purpose switching applications
- High conductance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "T4"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Forward Continuous Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current at $t = 1 \mu\text{s}$ at $t = 100 \text{ ms}$	I_{FSM}	2 1	A
Power Dissipation	P_{tot}	150	mW
Thermal Resistance Junction to Ambient Air	R_{eJA}	833	°C/W
Operating Temperature Range	T_j	- 55 to + 150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10 \mu\text{A}$	$V_{(BR)R}$	75	-	V
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at $V_R = 75 \text{ V}$ at $V_R = 20 \text{ V}$ at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$	I_R	- - - -	1 25 50 30	μA nA μA μA
Total Capacitance at $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R, I_F = I_R = 10 \text{ mA}, R_L = 100 \Omega$	t_{rr}	-	4	ns

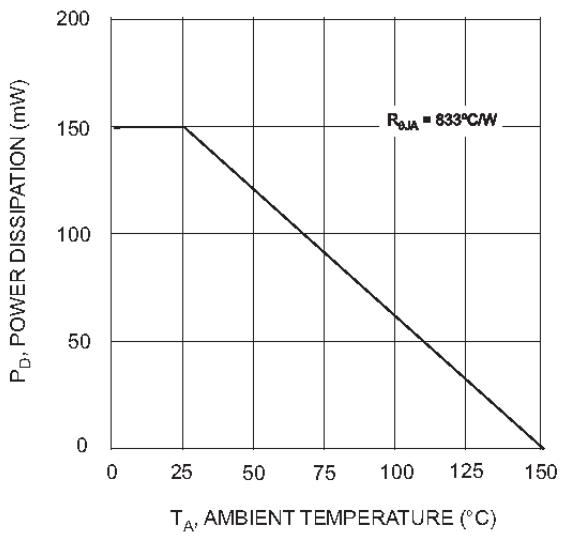


Fig. 1 Derating Curve

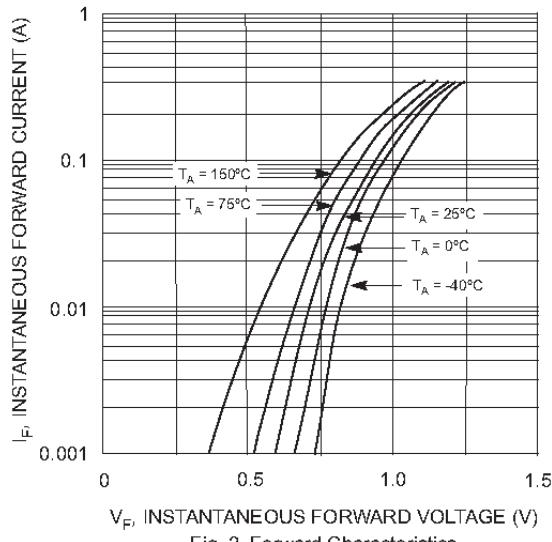


Fig. 2 Forward Characteristics

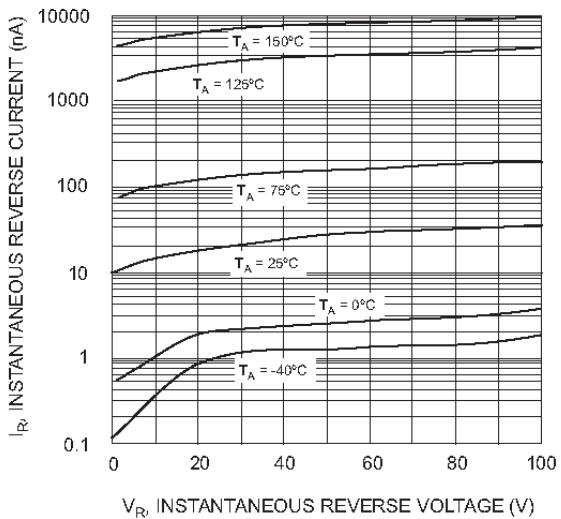


Fig. 3 Typical Reverse Characteristics

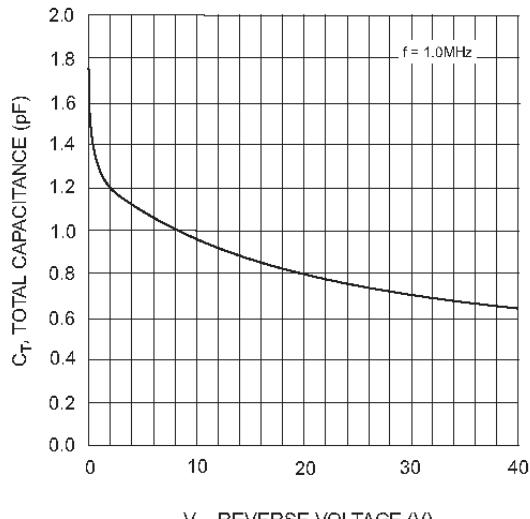


Fig. 4 Typical Capacitance vs. Reverse Voltage